

Electrically driven robust tuning of lattice thermal conductivity

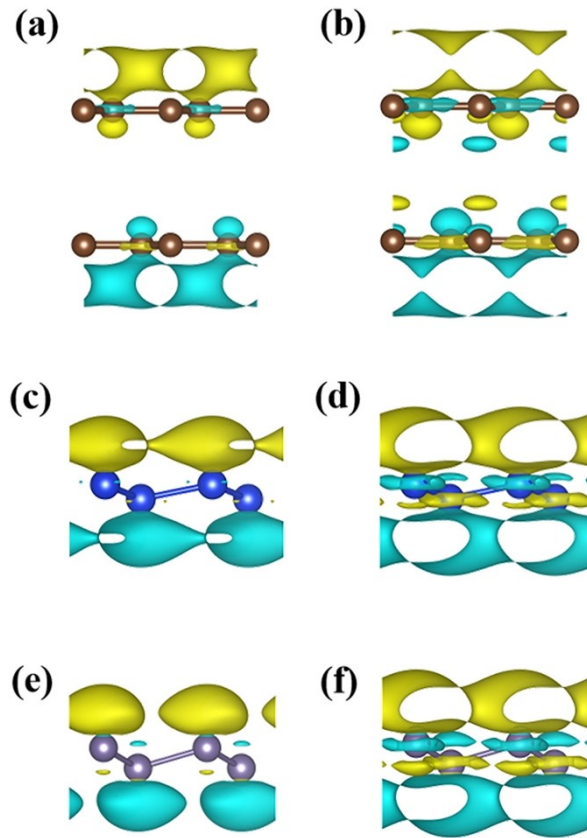
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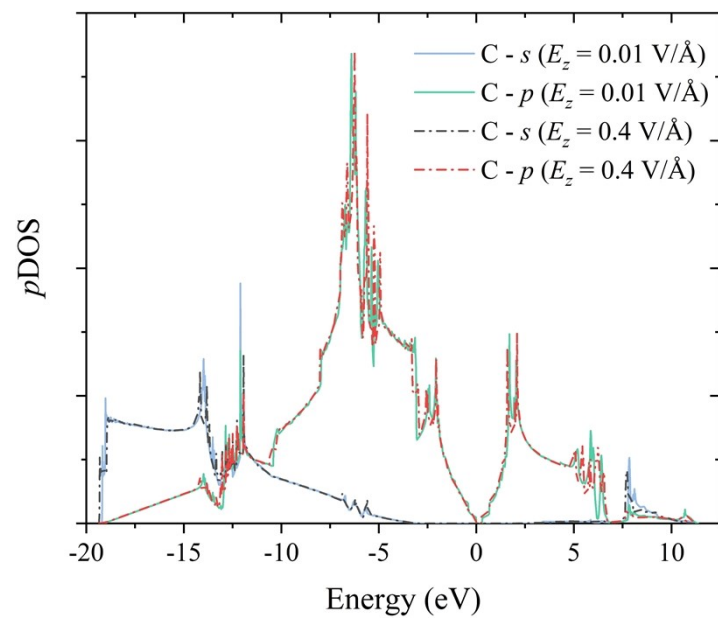
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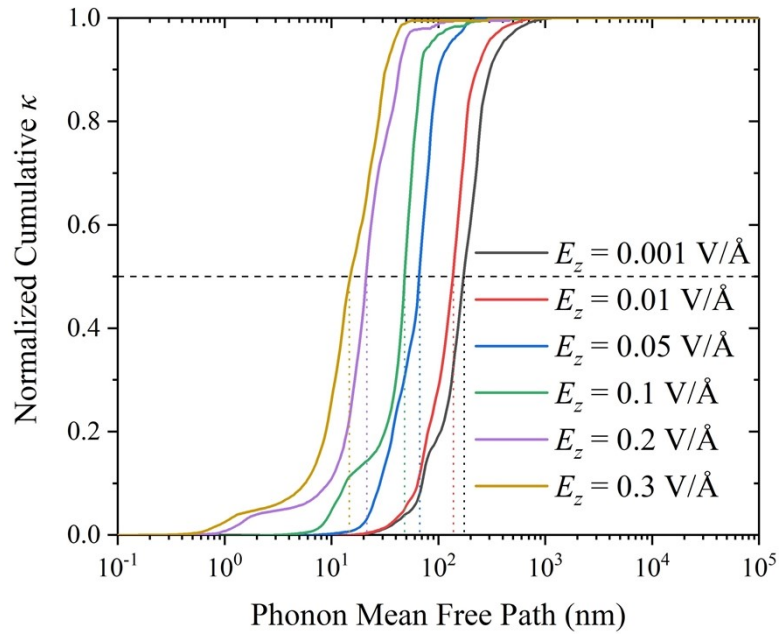
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Supplemental Fig. S1 The difference in charge density under typical electric field in 0.05 (a,c,e) and 0.1 eV/Å (b,d,f) for bilayer graphene (a, b), silicene (c, d), germanene (e, f). ($\Delta\rho = \rho(E_z) - \rho(E_z = 0)$) (yellow: positive accumulation of charge, blue: negative depletion of charge). The isosurface is set at 2×10^{-5} .



Supplemental Fig. S2 The projected density of states (*p*DOS) of C atoms with external electric field in bilayer graphene.



Supplemental Fig. S3 The normalized cumulative κ with respect to the phonon mean free path (MFP) for AB stacking bilayer graphene.